





75V NPN LOW SATURATION MEDIUM POWER TRANSISTOR

Features

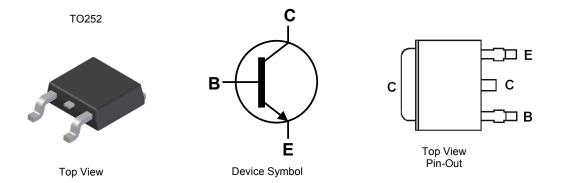
- BV_{CEO} > 75V
- I_C = 5A high Continuous Collector Current
- Up to 10A Peak Current
- $R_{SAT} = 70m\Omega$ for a low equivalent On-Resistance
- Low Saturation Voltage
- hFE specified up to 10A for a high gain hold up
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 63
- Weight: 0.34 grams (approximate)

Application

- DC DC converters
- Power Switches
- Motor Control
- Automotive Circuits
- Inverter Circuits



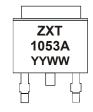
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXT1053AKTC	AEC-Q101	ZXT1053A	13	16	2,500
ZXT1053AKQTC	Automotive	ZXT1053A	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q10x qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



ZXT1053AK = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 09 = 2009) WW = Week Code (01 – 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	75	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	5	A
Peak Pulse Collector Current	Ісм	10	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		2.1		
Power Dissipation	(Note 7)	P_{D}	3.4	W	
	(Note 8)		4.0		
	(Note 6)		59		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	36	°C/W	
	(Note 8)		32		
Thermal Resistance, Junction to Leads (Note 9)		$R_{ heta JL}$	2.97	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

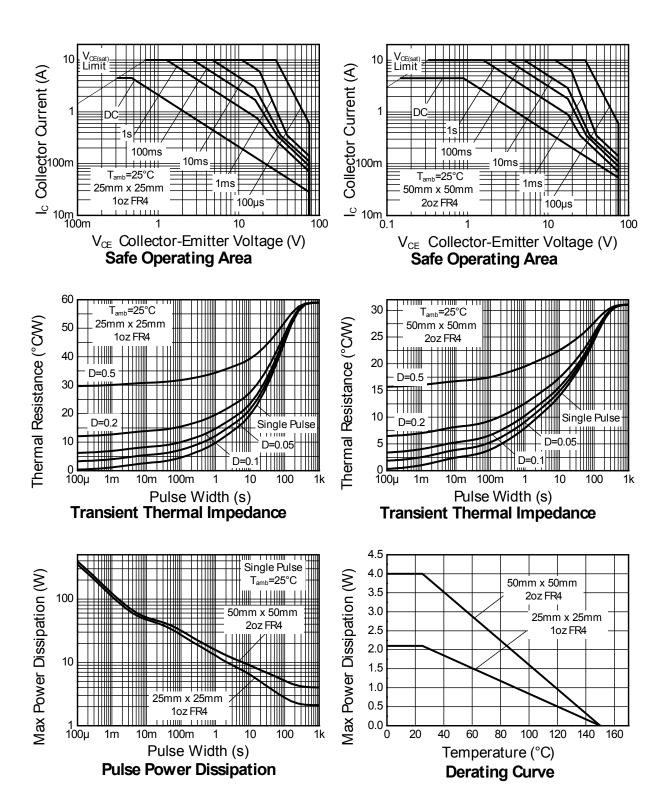
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note (6), except the device is surface mounted on 25mm x 25mm with 2oz copper.
- 8. Same as note (6), except the device is surface mounted on 50mm x 50mm with 2oz copper.
- Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





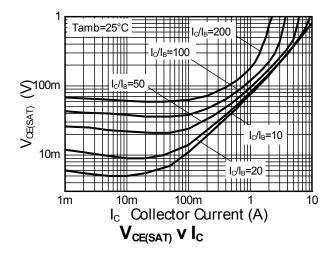
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

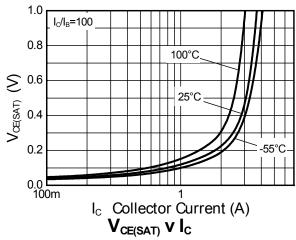
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	150	240	_	V	$I_{C} = 100 \mu A$
Collector-Base Breakdown Voltage	BV _{CES}	150	240	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV_CEO	75	90	_	V	I _C = 10mA
Collector-Emitter Breakdown Voltage	BV_CEV	150	240	_	V	$I_C = 1\mu A, V_{EB} = 1V$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.7	_	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	1	<1	10	nA	V _{CB} = 120V
Emitter Cutoff Current	I _{EBO}		<1	10	nA	V _{EB} = 6V
Emitter Cutoff Current	I _{CES}	_	<1	10	nA	V _{CE} = 120V
DC current transfer Static ratio (Note 9)	h _{FE}	260 300 50 10	375 450 75 25	_ 1200 _ _	_	$I_C = 10 \text{mA}, V_{CE} = 2 \text{V}$ $I_C = 1 \text{A}, V_{CE} = 2 \text{V}$ $I_C = 5 \text{A}, V_{CE} = 2 \text{V}$ $I_C = 10 \text{A}, V_{CE} = 2 \text{V}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	11111	19 70 120 140 350	30 95 160 190 460	mV	$I_C = 0.2A$, $I_B = 20mA$ $I_C = 1A$, $I_B = 100mA$ $I_C = 1A$, $I_B = 10mA$ $I_C = 2A$, $I_B = 100mA$ $I_C = 5A$, $I_B = 200mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	I	1.0	1.1	V	I _C = 5A, I _B = 200mA
Base-Emitter Turn-on Voltage (Note 11)	$V_{BE(on)}$	I	0.925	1.05	V	$I_C = 5A, V_{CE} = 2V$
Transitional Frequency	f_{T}	1	140	1	MHz	I _C = 50mA, V _{CE} = 10V f = 100MHz
Output capacitance	Сово		21	30	pF	V _{CB} = 10V, f = 1MHz,
Switching times	t _{ON} t _{OFF}	_	162 900	_	nS	I _C = 2A, V _{CC} = 50V, I _{B1} = I _{B2} = 20mA

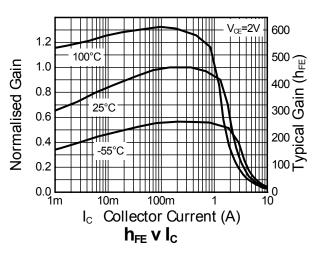
Notes: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

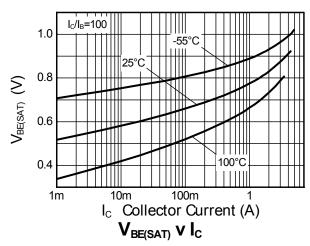


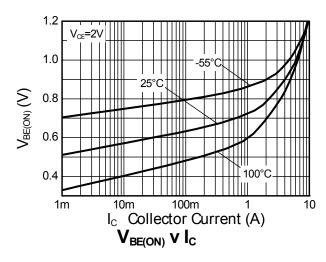
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







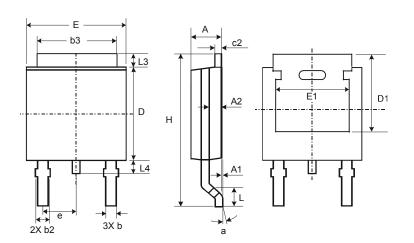






Package Outline Dimensions

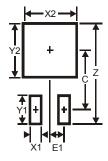
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
c2	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	_	_	
е	_	_	2.286	
Е	6.45	6.70	6.58	
E1	4.32	_	_	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	_	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
F1	2.3





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